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| Record Nr. | UNISA996213123503316 |
| Autore | Sandford Robert W. |
| Titolo | Ecology & wonder in the Canadian Rocky Mountain Parks World Heritage Site [[electronic resource] /] / Robert William Sandford ; with a foreword by James Thorsell |
| Pubbl/distr/stampa | Athabasca University Press, 2010<br>Edmonton, Alberta : , : AU Press, , 2010<br>©2010 |
| ISBN | 1-282-85197-7<br>9786612851971<br>1-897425-58-9 |
| Descrizione fisica | 1 online resource (379 p.) |
| Disciplina | 333.7209712332 |
| Soggetti | National parks and reserves - Canadian Rocky Mountain Parks World Heritage Site (Alta. and B.C.) - Management<br>Environmental protection - Canadian Rocky Mountain Parks World Heritage Site (Alta. and B.C.)<br>Ecology - Canadian Rocky Mountain Parks World Heritage Site (Alta. and B.C.)<br>Canadian Rocky Mountain Parks World Heritage Site (Alta. and B.C.) Environmental conditions<br>Canadian Rocky Mountain Parks World Heritage Site (Alta. and B.C.) History |
| Lingua di pubblicazione | Inglese |
| Formato | Materiale a stampa |
| Livello bibliografico | Monografia |
| Nota di bibliografia | Includes bibliographical references and index. |
| Nota di contenuto | COVER PAGE; CONTENTS; FOREWORD; ACKNOWLEDGEMENTS; Overview Map; INVOCATION: The Magnificent Seven; PART ONE: The West We Had: Foundations of Place; 1 A Walk into the Past: Setting a Context of Place; 2 The Creation: Monumentality and Place; 3 The Creation: People and Place Before European Contact; 4 Exchanging What We Had for What We Want: The Fur Trade Era in the Canadian West; 5 The Coming of Death: Diminishment and Loss among the First Peoples of the West; PART TWO: The West We Have: Making the Mountains Our Home<br>6 Giving Meaning to Mountains and Making Them Ours: Mountaineering and the Aesthetics of Place7 Brushes with Eternity: |

Landscape Art and Photography in the Canadian Rockies; 8 Crystal and Cold Blue Chasms: The Literature of the Canadian Rocky Mountain Parks World Heritage Site; 9 Stemming the Tide of Loss: The Give and Take of Modern Management In and Around the Mountain Parks; 10 Countering Dispossession: Saving Our Unique Mountain Culture; The East Slope: Flowing Toward the Atlantic; 11 The Birthplace of Canada's National Park Ideal: Banff National Park
The North Slope: Flowing Toward the Arctic12 The Birthplace of Western and Northern Rivers: The Columbia Icefield and Jasper National Park; The West Slope: Flowing Toward the Pacific; 13 The Roof of the Canadian Rockies: Mount Robson Provincial Park; 14 Small, Remote, but Utterly Wild: Hamber Provincial Park; 15 The Geography of Wonder: Yoho National Park; 16 The Road to Radium: Kootenay National Park; 17 Matterhorn of the Rockies: Mount Assiniboine Provincial Park; PART THREE: The West We Want: Creating a Culture Worthy of Place
18 Respecting and Honouring the Great Bear: The Grizzly as a Symbol of the West We Want19 Seeing What Is Hidden in Plain Sight: Triumphing Over Diminishment and Loss; 20 Expanding the World Heritage Site Designation: Managing for Future Integrity Instead of Loss; 21 Creating a Culture Commensurate with Place; NOTES; INDEX; A; B; C; D; E; F; G; H; I; J; K; L; M; N; O; P; R; S; T; U; V; W; Y

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| Sommario/riassunto | Ecology & Wonder makes several remarkable claims: The greatest cultural achievement in the Western Canadian mountain region may be what has been preserved, not what has been developed. Protecting the spine of the Rocky Mountains will preserve crucial ecological functions. Because the process of ecosystem diminishment and species loss has been slowed, an ecological thermostat has been kept alive. This may well be an important defence against future climate change impacts in the Canadian west. Ecology & Wonder is a must-read for those who appreciate Western Canada's breathtaking landscape. |

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| Record Nr. | UNINA9910808037403321 |
| Autore | Ker Ming-Dou |
| Titolo | Transient-induced latchup in CMOS integrated circuits / / Ming-Dou Ker and Sheng-Fu Hsu |
| Pubbl/distr/stampa | Singapore ; ; Hoboken, NJ, : Wiley, c2009 |
| ISBN | 9786612382185<br>9781282382183<br>1282382187<br>9780470824092<br>0470824093<br>9780470824085<br>0470824085 |
| Edizione | [1st ed.] |
| Descrizione fisica | 1 online resource (265 p.) |
| Altri autori (Persone) | HsuSheng-Fu |
| Disciplina | 621.3815<br>621.39/5 |
| Soggetti | Metal oxide semiconductors, Complementary - Defects<br>Metal oxide semiconductors, Complementary - Reliability |
| Lingua di pubblicazione | Inglese |
| Formato | Materiale a stampa |
| Livello bibliografico | Monografia |
| Note generali | Description based upon print version of record. |
| Nota di bibliografia | Includes bibliographical references and index. |
| Nota di contenuto | Physical Mechanism of TLU under the System-Level ESD Test -- Component-Level Measurement for TLU under System-Level ESD Considerations -- TLU Dependency on Power-Pin Damping Frequency and Damping Factor in CMOS Integrated Circuits -- TLU in CMOS ICs in the Electrical Fast Transient Test -- Methodology on Extracting Compact Layout Rules for Latchup Prevention -- Special Layout Issues for Latchup Prevention -- TLU Prevention in Power-Rail ESD Clamp Circuits -- Appendix A: Practical Application Extractions of Latchup Design Rules in a 0.18-mm 1.8 V/3.3V Silicided CMOS Process. |
| Sommario/riassunto | "Transient-Induced Latchup in CMOS Integrated Circuits equips the practicing engineer with all the tools needed to address this regularly occurring problem while becoming more proficient at IC layout. Ker and Hsu introduce the phenomenon and basic physical mechanism of latchup, explaining the critical issues that have resurfaced for CMOS |

technologies. Once readers can gain an understanding of the standard practices for TLU, Ker and Hsu discuss the physical mechanism of TLU under a system-level ESD test, while introducing an efficient component-level TLU measurement setup. The authors then present experimental methodologies to extract safe and area-efficient compact layout rules for latchup prevention, including layout rules for I/O cells, internal circuits, and between I/O and internal circuits. The book concludes with an appendix giving a practical example of extracting layout rules and guidelines for latchup prevention in a 0.18-micrometer 1.8V/3.3V silicided CMOS process."--Publisher's description.